

## **INCHANGE SEMICONDUCTOR**

## *isc* Silicon PNP Darlingtion Power Transistor

# 2SB1020

### DESCRIPTION

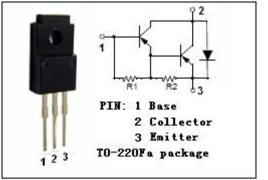
- High DC C urrent Gain-: h<sub>FE</sub>= 2000(Min.)@I<sub>C</sub>= -3A
- Low Collector Saturation Voltage-: V<sub>CE(sat)</sub>= -1.5V(Max)@I<sub>C</sub>= -3A
- · Good Linearity of hFE
- Complement to Type 2SD1415
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

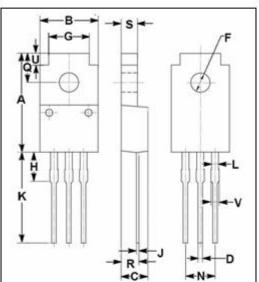
### **APPLICATIONS**

- High power switching applications.
- · Hammer drive, pulse motor drive applications.

SYMBOL	PARAMETER	VALUE	UNIT	
Vсво	Collector-Base Voltage	e -100		
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	-5	V	
lc	Collector Current-Continuous	-7	A	
IB	Base Current-Continuous	-0.2	A	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	2	W	
	Collector Power Dissipation @ $T_C$ =25°C	30		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





	m	m
DIM	MIN	MAX
A	16.85	17.15
В	9.54	10.10
С	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
Н	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

isc website: www.iscsemi.com



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## ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-100			V
Vce(sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -6mA			-1.5	V
V <sub>CE</sub> (sat)-2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -7A; I <sub>B</sub> = -14mA			-2.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -6mA			-2.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-4.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -3V	2000		15000	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -7A; V <sub>CE</sub> = -3V	1000			



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